

N-CHANNEL MOSFET (dual transistors)

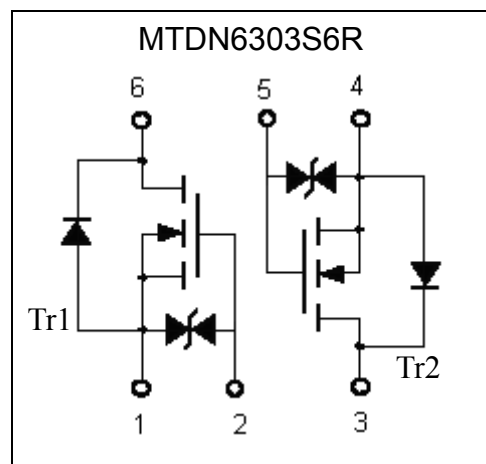
MTDN6303S6R

BV_{DSS}	20V
I_D	760mA
$R_{DS(on)}@V_{GS}=4.5V, I_D=600mA$	370m Ω (typ)
$R_{DS(on)}@V_{GS}=2.5V, I_D=400mA$	500m Ω (typ)
$R_{DS(on)}@V_{GS}=1.8V, I_D=350mA$	1.1 Ω (typ)

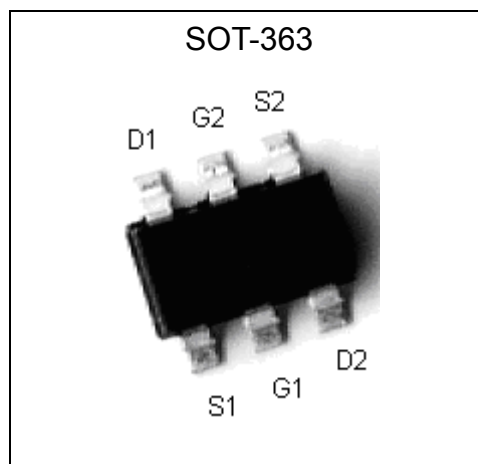
Features

- Low on-resistance
- High ESD capability
- High speed switching
- Low-voltage drive(1.8V)
- Pb-free lead plating and halogen-free package

Equivalent Circuit



Outline



The following characteristics apply to both Tr1 and Tr2

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current @ $T_A=25^\circ C, V_{GS}=4.5V$ (Note 3)	I_D	760	mA
Continuous Drain Current @ $T_A=85^\circ C, V_{GS}=4.5V$ (Note 3)		550	
Pulsed Drain Current (Notes 1, 2)	I_{DM}	3	A
Maximum Power Dissipation (Note 3)	P_D	$T_A=25^\circ C$ 300	mW
		$T_A=85^\circ C$ 160	
ESD susceptibility		2000 (Note 4)	V
Operating Junction and Storage Temperature	T_j, T_{stg}	-55~+150	$^\circ C$

- Note : 1. Pulse width limited by maximum junction temperature.
2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Surface mounted on 1 in² copper pad of FR-4 board, $t \leq 5s$.
4. Human body model, 1.5k Ω in series with 100pF



Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Ambient(PCB mounted) (Note)	Rth,ja	417	°C/W

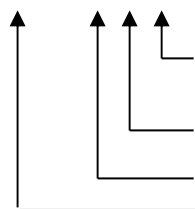
Note : Surface mounted on 1 in² copper pad of FR-4 board, t₅s.Electrical Characteristics (T_j=25°C, unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	20	-	-	V	V _{GS} =0, I _D =250μA
ΔBV _{DSS} /ΔT _j	-	0.02	-	V/°C	Reference to 25°C, I _D =1mA
V _{GS(th)}	0.5	0.92	1.2	V	V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	-	-	±10	μA	V _{GS} =±8V, V _{DS} =0
I _{DSS}	-	-	1		V _{DS} =20V, V _{GS} =0
	-	-	10		V _{DS} =16V, V _{GS} =0 (T _j =70°C)
*R _{DS(ON)}	-	370	450	mΩ	V _{GS} =4.5V, I _D =600mA
	-	500	650		V _{GS} =2.5V, I _D =400mA
		1100	1300		V _{GS} =1.8V, I _D =350mA
*G _{FS}	-	1.4	-	S	V _{DS} =5V, I _D =600mA
Dynamic					
C _{iSS}	-	60	-	pF	V _{DS} =10V, V _{GS} =0, f=1MHz
C _{oSS}	-	14	-		
C _{rSS}	-	9	-		
t _{d(ON)}	-	4	-	ns	V _{DS} =10V, I _D =600mA, V _{GS} =10V R _G =3.3 Ω , R _D =16.7 Ω
t _r	-	10	-		
t _{d(OFF)}	-	15	-		
t _f	-	2	-		
Q _g	-	1.3	-	nC	V _{DS} =16V, I _D =600mA, V _{GS} =4.5V
Q _{gs}	-	0.3	-		
Q _{gd}	-	0.5	-		
Source-Drain Diode					
*V _{SD}	-	0.81	1.2	V	V _{GS} =0V, I _S =500mA

*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

Ordering Information

Device	Package	Shipping
MTDN6303S6R-0-T1-G	SOT-363 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel



Environment friendly grade : S for RoHS compliant products, G for RoHS compliant and green compound products

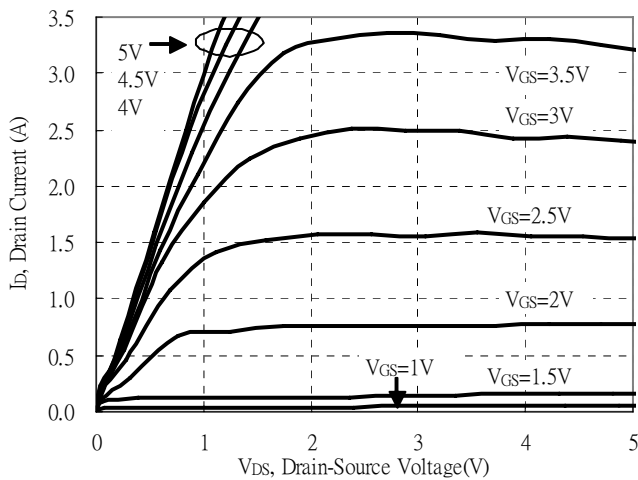
Packing spec, T1 : 3000 pcs / tape & reel, 7" reel

Product rank, zero for no rank products

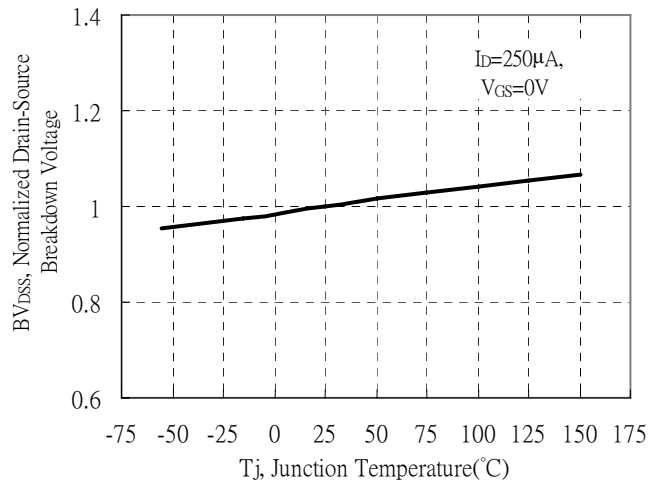
Product name

Typical Characteristics

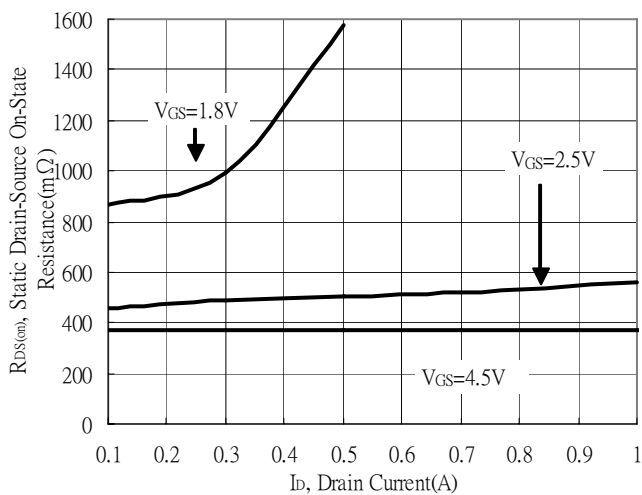
Typical Output Characteristics



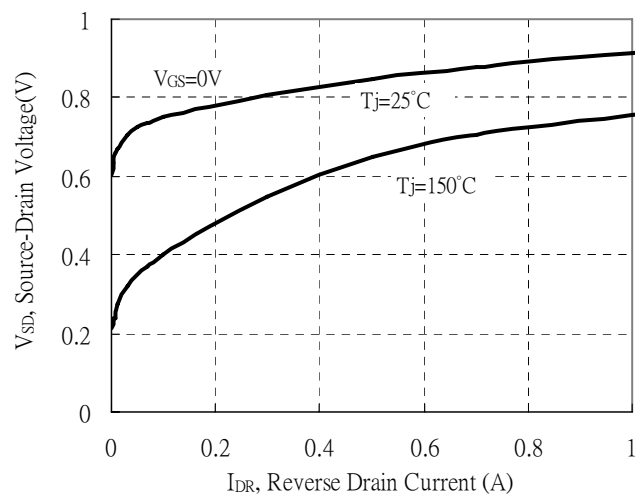
Breakdown Voltage vs Ambient Temperature



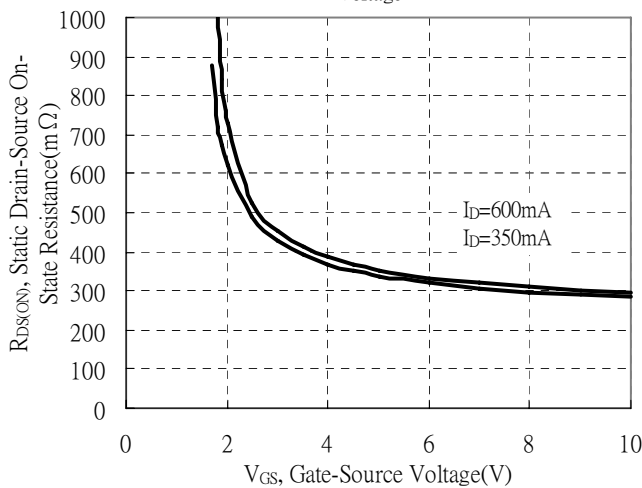
Static Drain-Source On-State resistance vs Drain Current



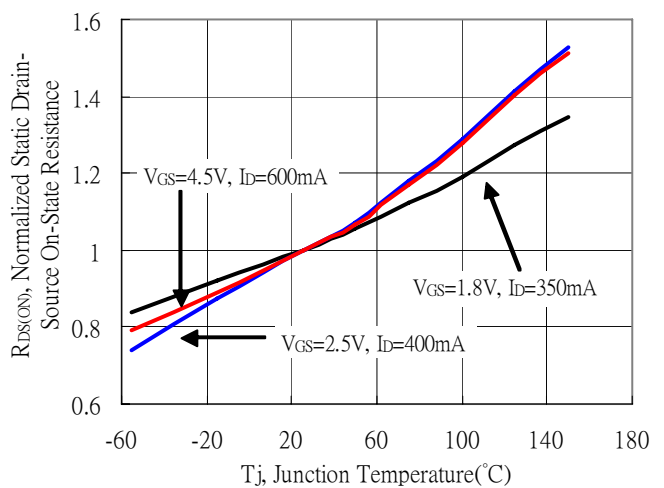
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

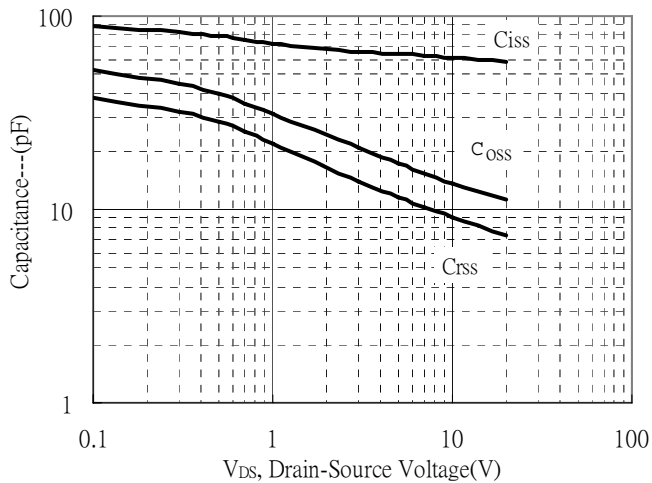


Drain-Source On-State Resistance vs Junction Temperature

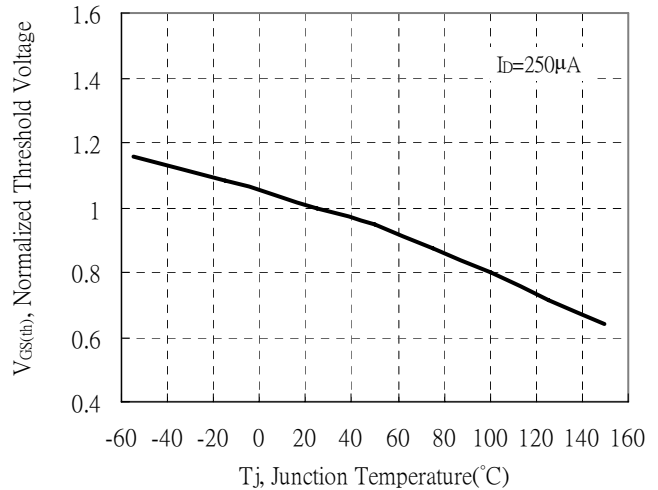


Typical Characteristics(Cont.)

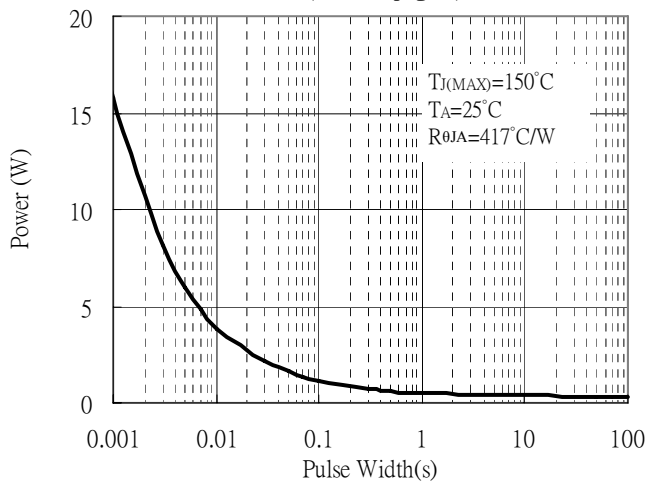
Capacitance vs Drain-to-Source Voltage



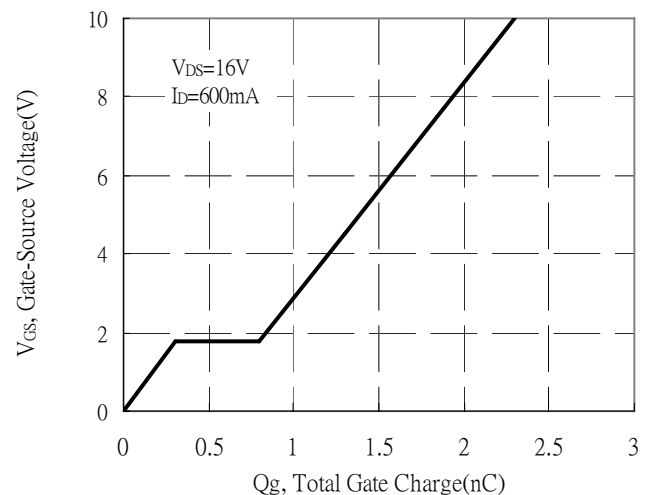
Threshold Voltage vs Junction Temperature



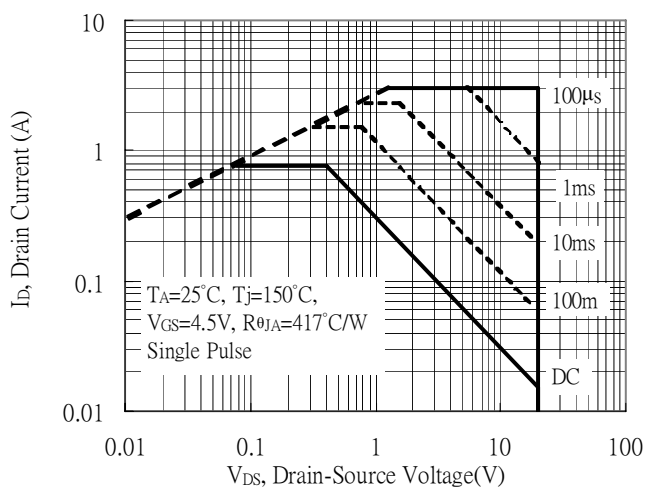
Single Pulse Power Rating, Junction to Ambient
 (Note on page 2)



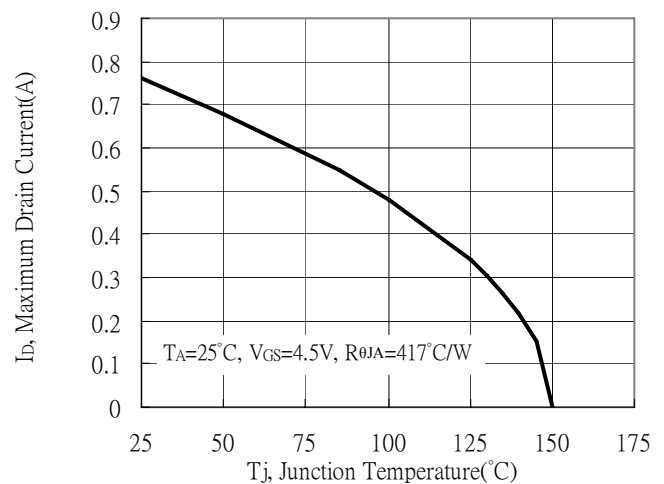
Gate Charge Characteristics



Maximum Safe Operating Area

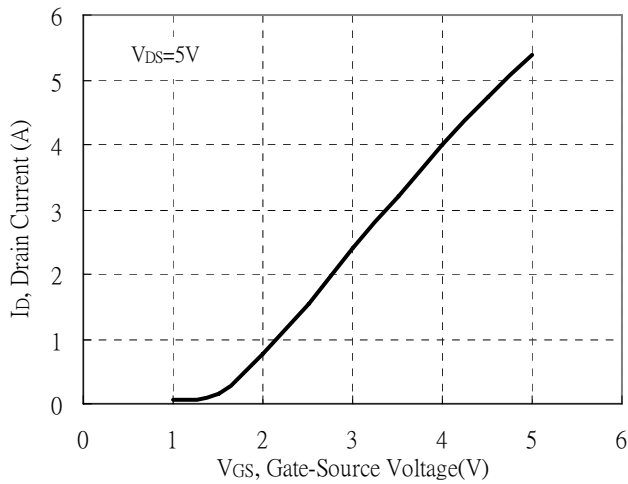


Maximum Drain Current vs Junction Temperature

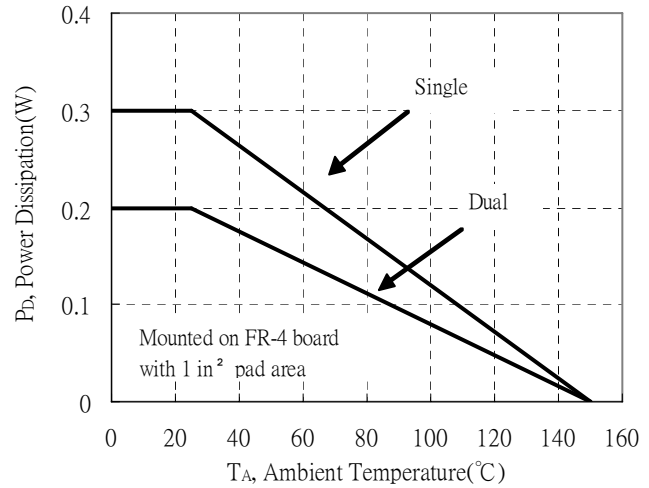


Typical Characteristics(Cont.)

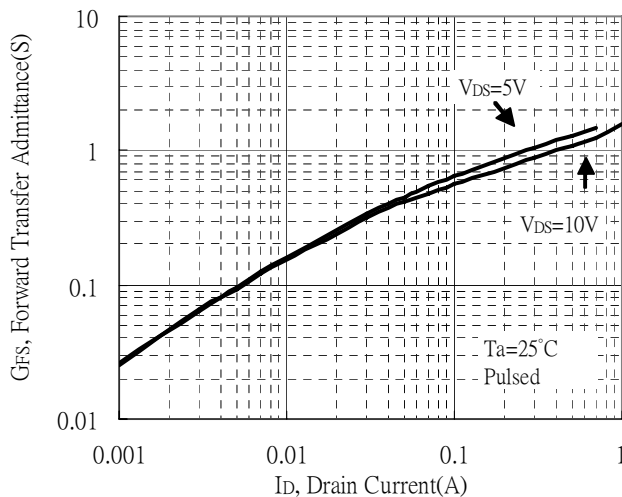
Typical Transfer Characteristics



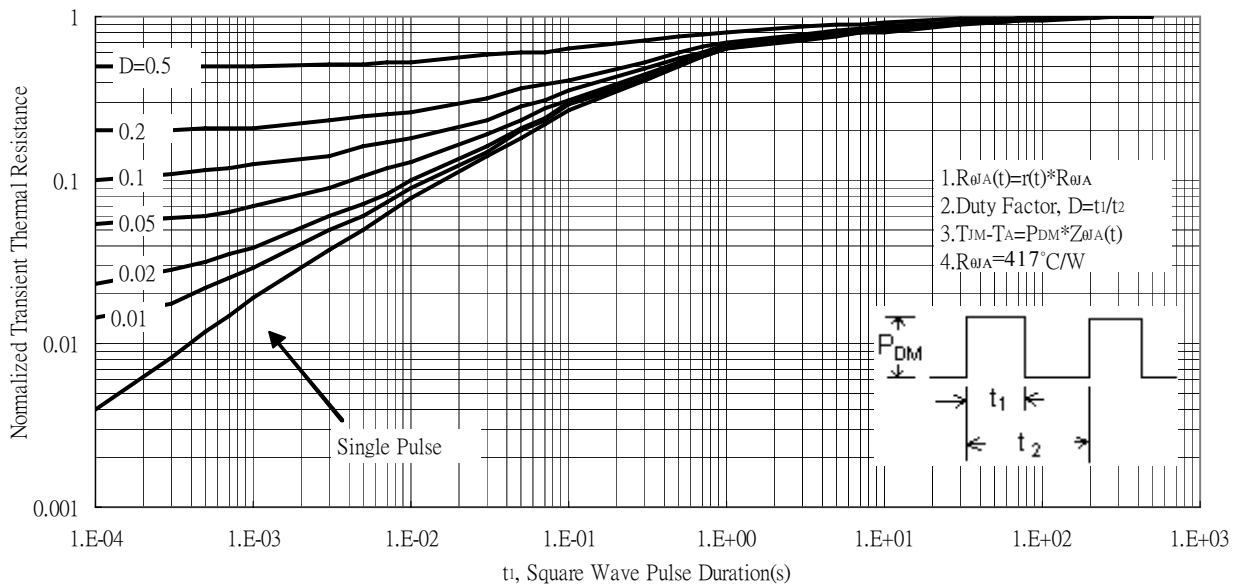
Power Derating Curve



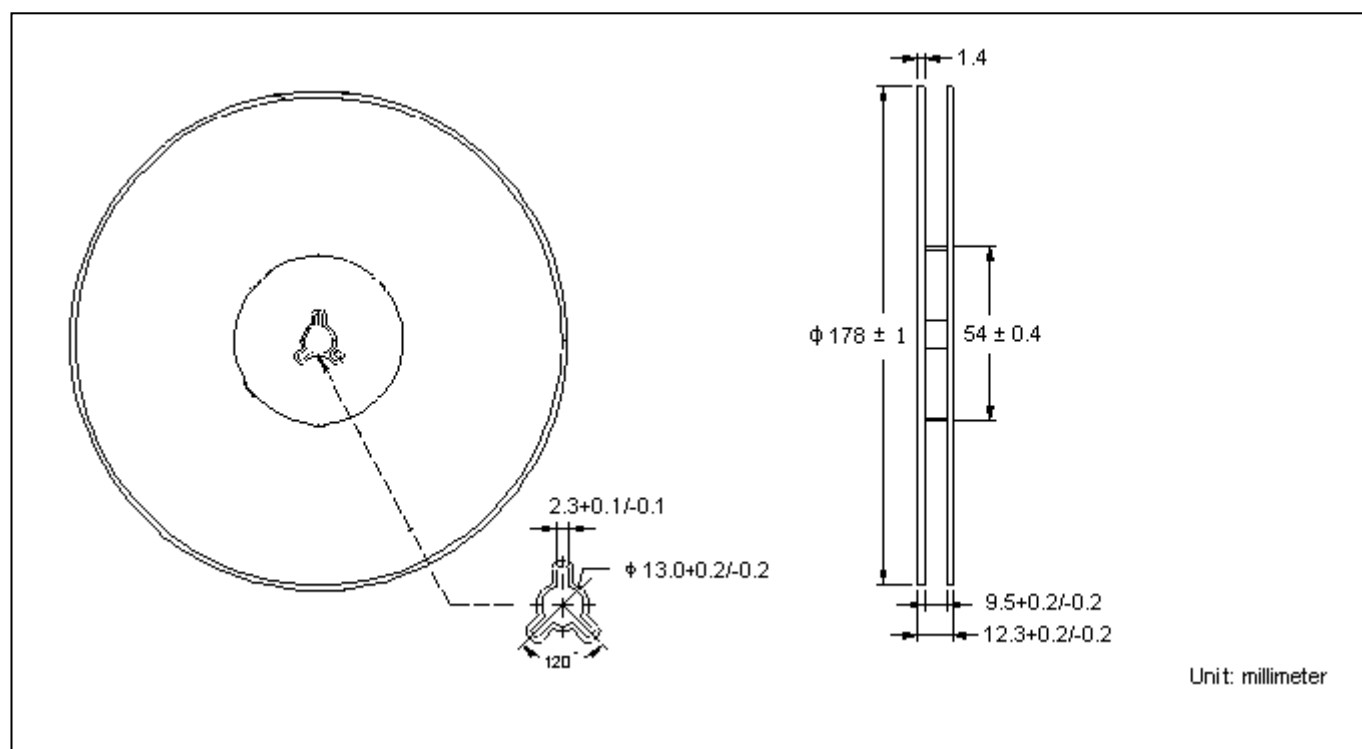
Forward Transfer Admittance vs Drain Current



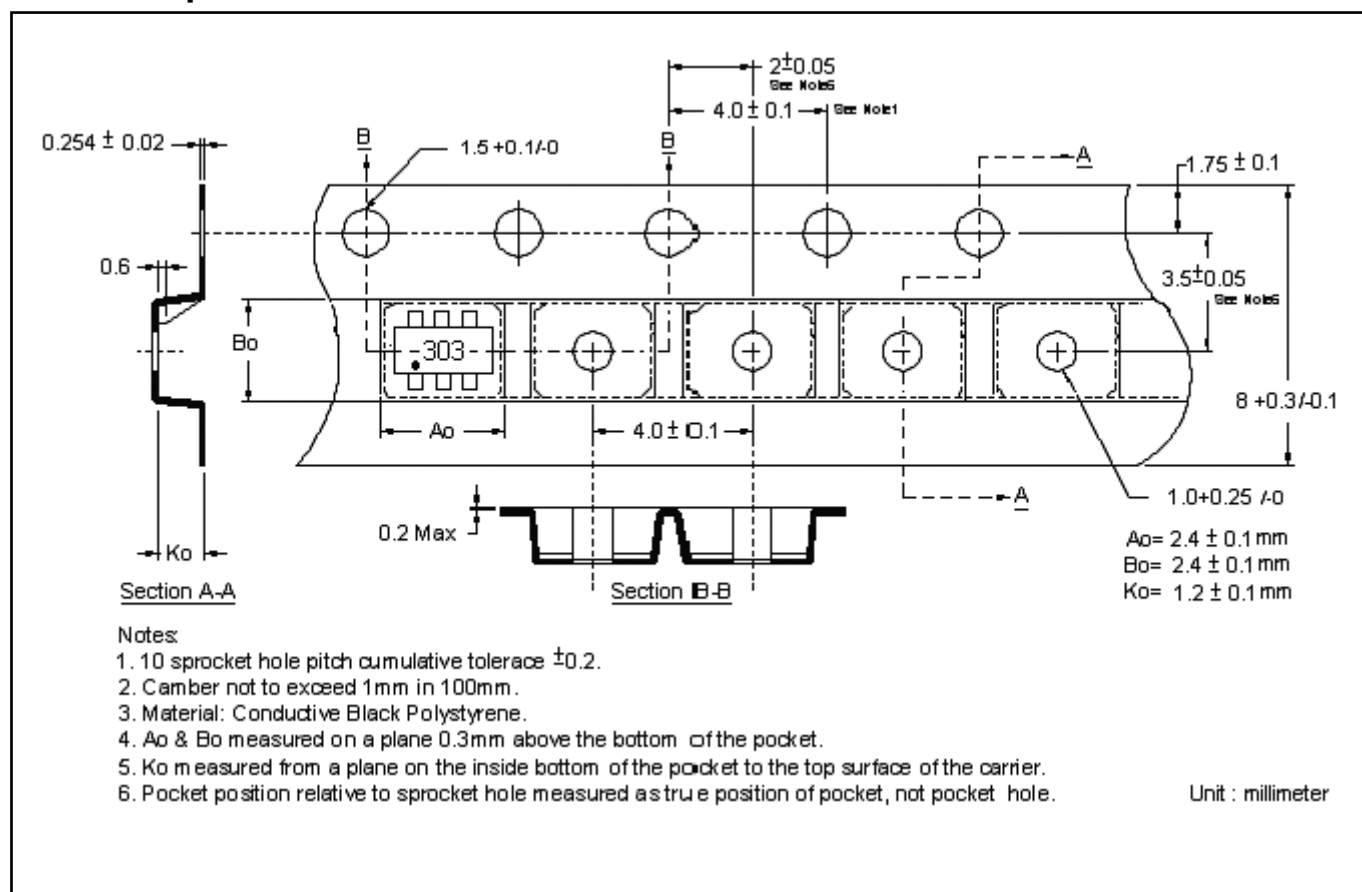
Transient Thermal Response Curves



Reel Dimension



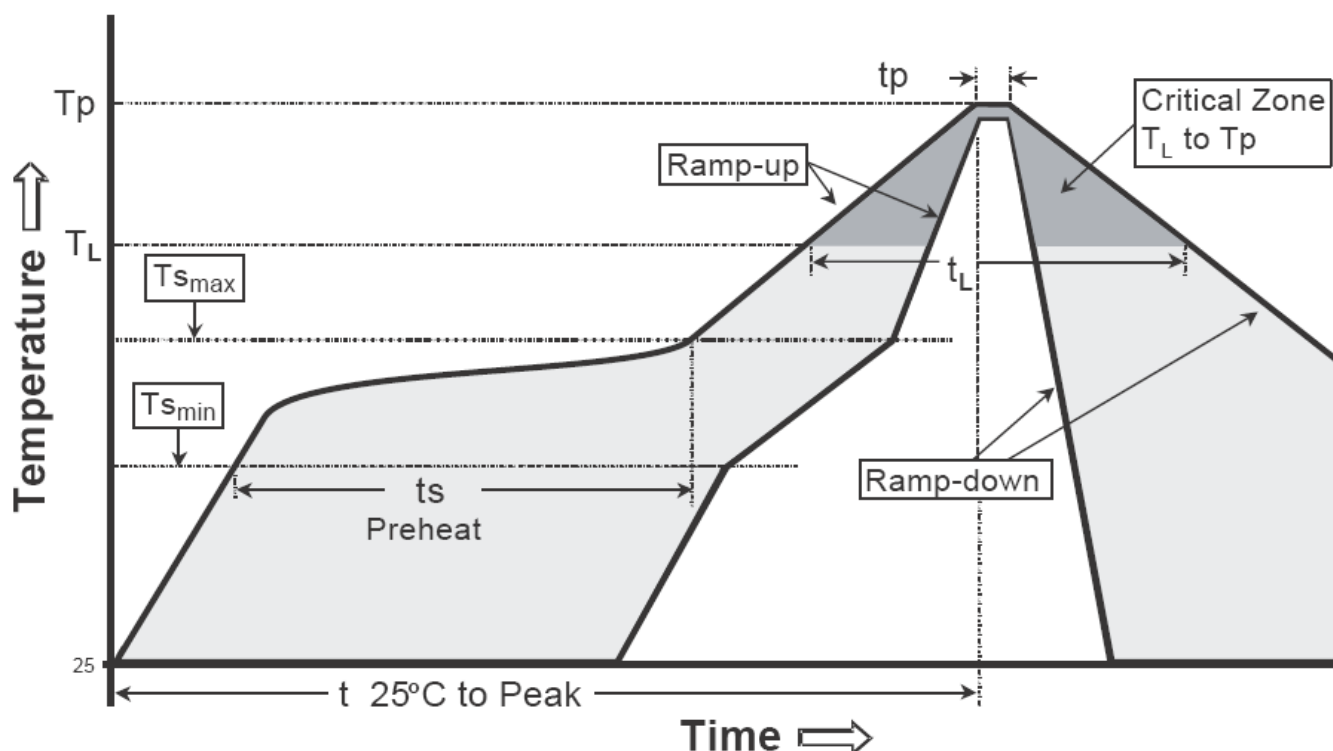
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

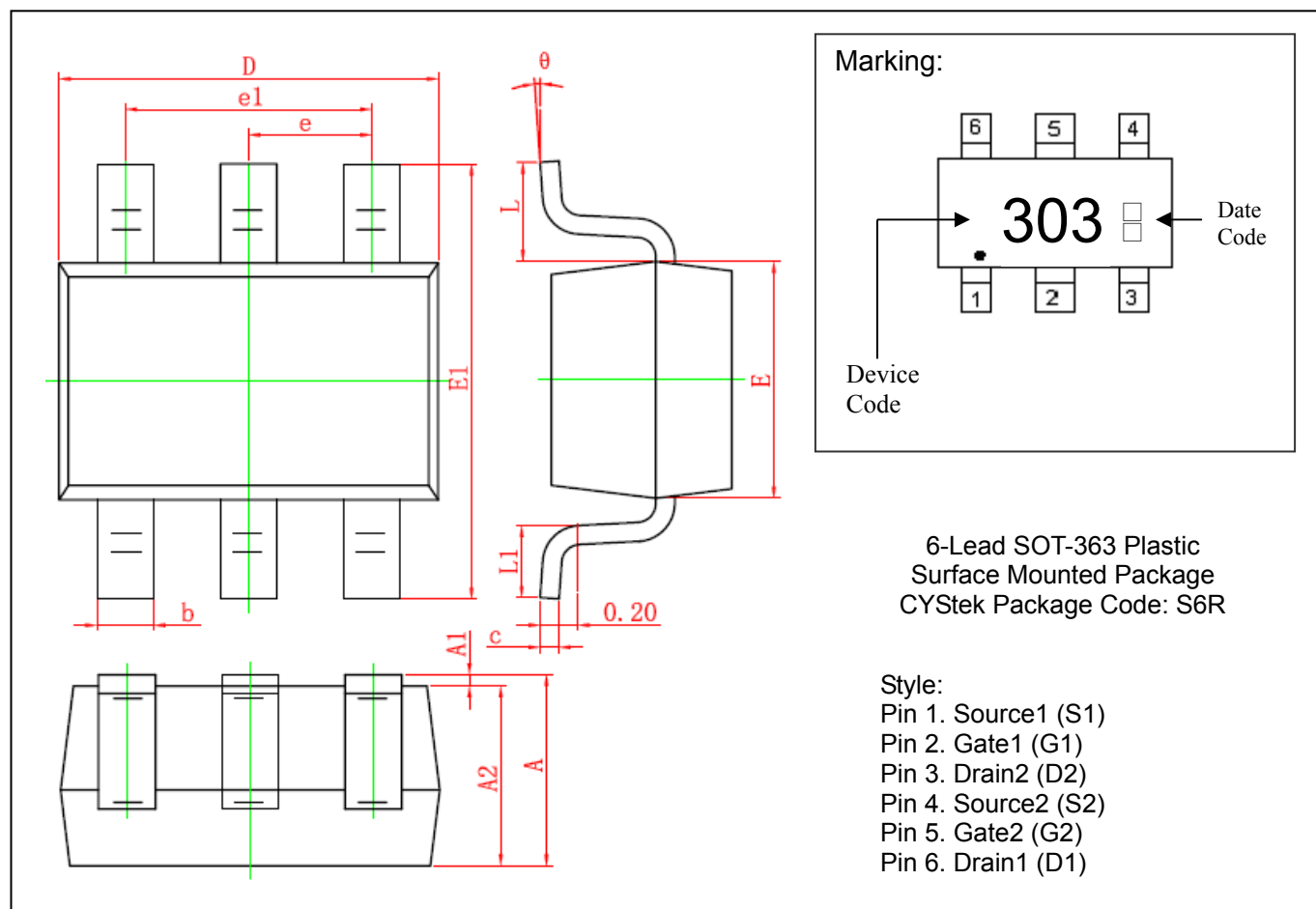
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (Tl)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(Tp)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-363 Dimension



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	E1	2.150	2.450	0.085	0.096
A1	0.000	0.100	0.000	0.004	e	0.650	TYP	0.026	TYP
A2	0.900	1.000	0.035	0.039	e1	1.200	1.400	0.047	0.055
b	0.150	0.350	0.006	0.014	L	0.525	REF	0.021	REF
c	0.080	0.150	0.003	0.006	L1	0.260	0.460	0.010	0.018
D	2.000	2.200	0.079	0.087	θ	0°	8°	0°	8°
E	1.150	1.350	0.045	0.053					

Notes : 1. Controlling dimension : millimeters.

2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material :

- Lead : Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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